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 10581127 - GAU: 2895
 Sheet 1 of 2 **AP20 Rec'd PCT/PTO 30 MAY 2006**

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				ATTY DOCKET NO. 536-009.028		SERIAL NO. 10/581127 To be assigned			
				APPLICANT: B. HEINEMANN et al.					
				FILING DATE: Herewith		ART UNIT: To be assigned			
UNITED STATES PATENT DOCUMENTS									
EXAM. INITIAL		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE		
/DN/		2005/0023642	Feb. 03, 2005	Heinemann et al.					
		2003/0146477	Aug. 07, 2003	Krutsick					
		2003/0146468	Aug. 07, 2003	Gris et al.					
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FOREIGN PATENT DOCUMENTS									
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO		
/DN/		EP 0 746 038	Dec. 19, 2001	EP					
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/DN/	1	M. C. Wilson et al., "Process HJ: A 30 GHz NPN and 20 GHz PNP complementary bipolar process for high linearity RF circuits," IEEE BCTM 9.4, 1998, pp.164-167.							
/DN/	2	D. Knoll et al., "A flexible, low-cost, high performance SiGe:C BiCMOS process with a one-mask HBT module," IEEE, 2002.							
/DN/	3	B. Heinemann et al., "Novel collector design for high-speed SiGe:C HBTs," IEEE, 2002.							
/DN/	4	D. V. Singh et al., "Novel epitaxial p-Si/n-Si _{1-y} C _y /p-Si heterojunction bipolar transistors," IEEE, 2000.							
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/DN/	6	D. V. Singh et al., "Effect of band alignment and density of states on the collector current in p-Si/n-Si _{1-y} C _y /p-Si HBTs," IEEE Transactions on Electron Devices, Vol. 50, No. 2, February 2003, pp. 425-32.							
Examiner (To be assigned)				Date:					

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Sheet 2 of 2

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EXAM. INITIAL /DN/		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE		
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/DN/		6,222,250	April 24, 2001	Gomi					
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/DN/	10	S. J. Jeng et al., "A 210-GHz f_T SiGe HBT with a non-self-aligned structure," IEEE Electron Device Letters, Vol. 22, No. 11, November 2001.							
/DN/	11	J. D. Cressler et al., "A high-speed complementary silicon bipolar technology with 12-fJ power-delay product," IEEE Electron Device Letters, Vol. 14, No. 11, November 1993, pp. 523-526.							
/DN/	12	W. Klein et al., "75 GHz bipolar production technology for the 21st century," pp. 88-94. date unknown							
Examiner (To be assigned) /David Nhu/				Date: 06/06/2010					